XBS304S17R-G



Schottky Barrier Diode, 3A, 40V Type

■FEATURES

Forward Voltage : V_F=0.465V (TYP.)

Forward Current : $I_{F(AVE)}$ =3A

Repetitive Peak Reverse Voltage : V_{RM}=40V

■APPLICATIONS

- Rectification
- Protection against reverse connection of battery

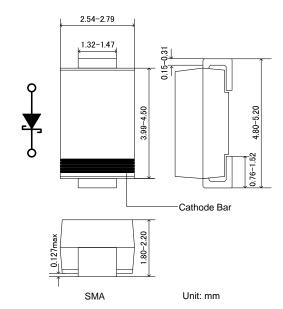
■ ABSOLUTE MAXIMUM RATINGS

Ta=25°C

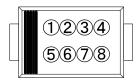
PARAMETER	SYMBOL	RATINGS	UNIT	
Repetitive Peak Reverse Voltage	Vrm	40	V	
Reverse Voltage (DC)	Itage (DC) VR 40		V	
Forward Current (Average)	IF(AVE)	VE) 3		
Non Continuous	IFSM	60	Α	
Forward Surge Current ^{*1}	IFSM	60	A	
Junction Temperature	Tj	125	လူ	
Storage Temperature Range	Tstg	-55~+150	°C	

^{*1:} Non continuous high amplitude 60Hz half-sine wave.

■PACKAGING INFORMATION



■MARKING RULE



①23456: 304S17(Product Number)

: Assembly Lot Number

■PRODUCT NAME

PRODUCT NAME	DEVICE ORIENTATION		
XBS304S17R-G	SMA (Halogen & Antimony free)		
XBS304S17R	SMA		

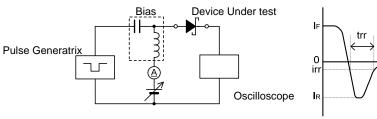
^{*} The "-G" suffix indicates that the products are Halogen and Antimony free as well as being fully RoHS compliant.

■ELECTRICAL CHARACTERISTICS

Ta=25°C

PARAMETER SYME	SYMBOL	TEST CONDITIONS	LIMITS			UNIT
	STIVIBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Forward Voltage ——	VF1	I _F =200 μ A	-	0.135	=	V
	VF2	I _F =3A	-	0.465	0.51	V
Reverse Current	l _{R1}	V _R =20V	-	5	-	μΑ
	IR2	V _R =40V	-	15	300	μΑ
Inter-Terminal Capacity	Ct	V _R =1V , f=1MHz	-	180	-	pF
Reverse Recovery Time*2	trr	I _F =I _R =10mA , irr=1mA	-	82	=	ns

^{*2 :} trr measurement circuit

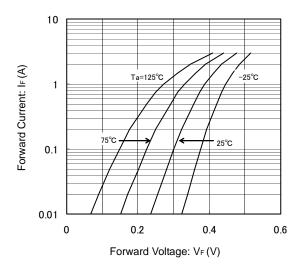


^{*} The device orientation is fixed in its embossed tape pocket.

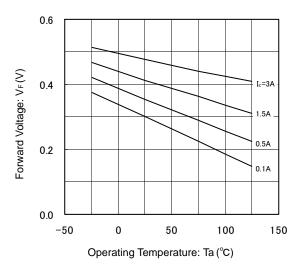
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■TYPICAL PERFORMANCE CHARACTERISTICS

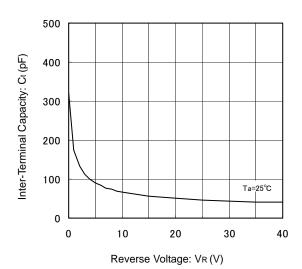
(1) Forward Current vs. Forward Voltage



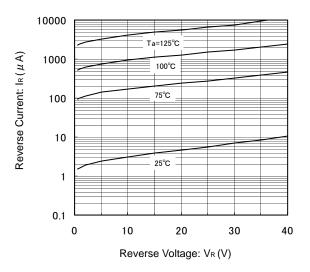
(3) Forward Voltage vs. Operating Temperature



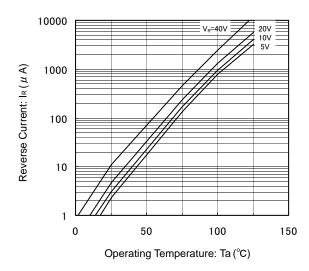
(5) Inter-Terminal Capacity vs. Reverse Voltage



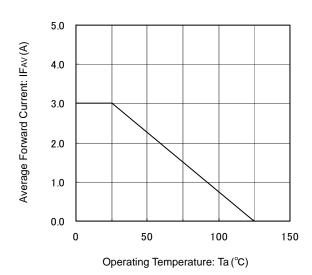
(2) Reverse Current vs. Reverse Voltage



(4) Reverse Current vs. Operating Temperature



(6) Average Forward Current vs. Operating Temperature



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